WNSC2D12650T



Silicon Carbide Diode Rev.01 - 30 November 2021

Product data sheet

1. General description

Silicon Carbide Schottky diode in a DFN 8*8 plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			650			V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _c ≤ 146 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>		12		A	
Tj	junction temperature			175		°C	
Symbol	Parameter	Conditions	Min Typ Max		Unit		
Static ch	aracteristics						
V _F	forward voltage	I _F = 12 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.8	2.2	V
Dynamic	characteristics	·				,	
Q _r	recovered charge	$I_F = 12 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	17.5	-	nC

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	[]	к-Ң-А
2	n.c.	not connected	5	001aaa020
3	А	anode		
4	А	anode		
5	К	mounting base; connected to cathode	1 2 3 4	

6. Ordering information

Table 3. Ordering information								
ickage (Orderable part number	Packing	Small packing	Package	Package			
me		method	quantity	version	issue date			
N8*8	WNSC2D12650TJ	Таре	3000	DFN8X8N	25-Dec-2019			
m	ne	ne	ne method	ne method quantity	ne method quantity version			

7. Marking

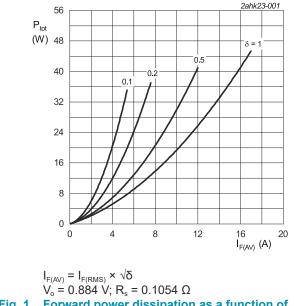
Table 4. Marking codes					
Type number	Marking codes				
WNSC2D12650T	WNSC2D 12650T				

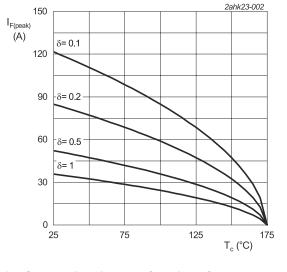
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V _R	reverse voltage	DC	650	V
$I_{F(AV)}$	average forward current	δ = 0.5; square-wave pulse; T _c ≤ 146 °C; Fig. 1; Fig. 2; Fig. 3	12	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _c ≤ 146 °C; square-wave pulse	24	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	60	А
	forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	600	А
l ² t	I ² t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms	18	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C

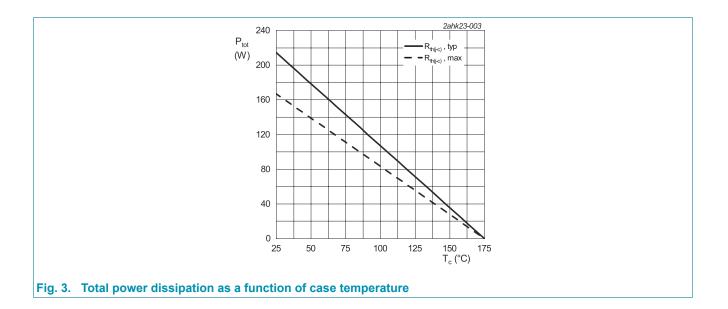






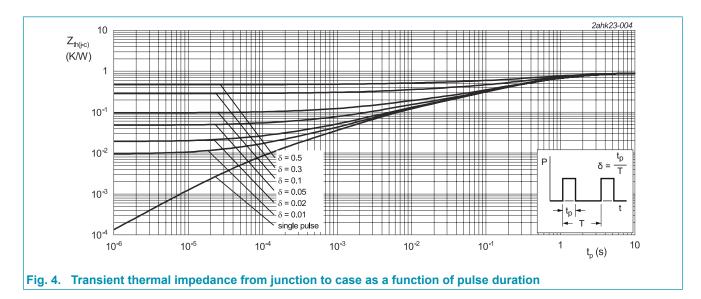
V_o = 0.884 V; R_s = 0.1054 Ω
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

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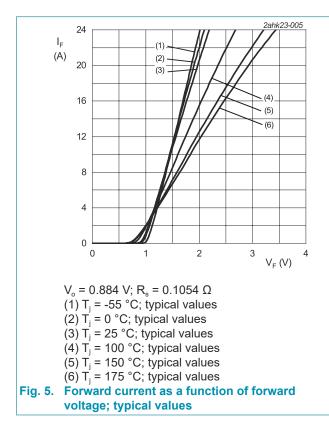
9. Thermal characteristics

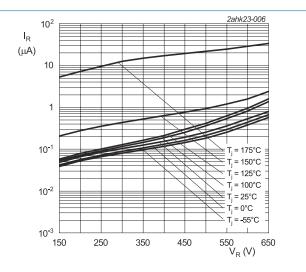
Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	<u>Fig. 4</u>	-	0.7	0.9	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W



10. Characteristics

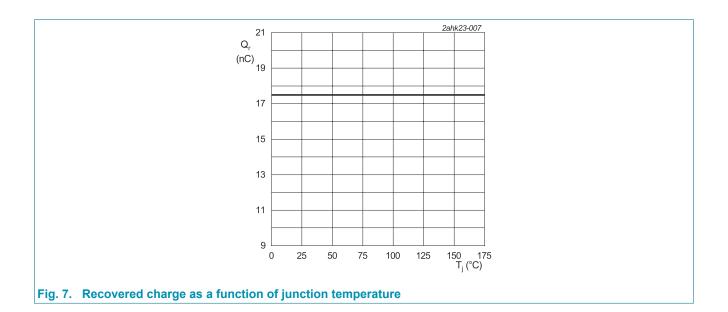
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward current	I _F = 12 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.8	2.2	V
		I _F = 12 A; T _j = 175 °C; <u>Fig. 5</u>	-	2	2.3	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>	-	0.6	60	μA
		V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u>	-	30	300	μA
Dynamic	characteristics		I			
Q _r	recovered charge	$I_F = 12 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	17.5	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	380	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	44	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	41	-	pF
E _{as}	non-repetitive avalanche energy	I _R = 4.6 A; L = 5 mH; T _{j(init)} = 25 °C	55	-	-	mJ



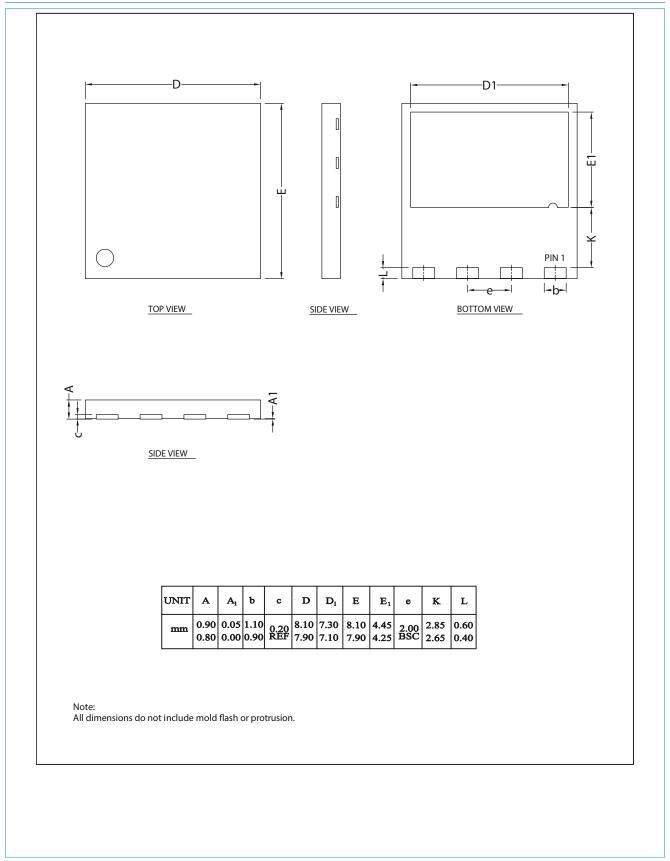




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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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